NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI AVD350** is high power Class C transistor, designed for avionics applications in 960-1215 MHz

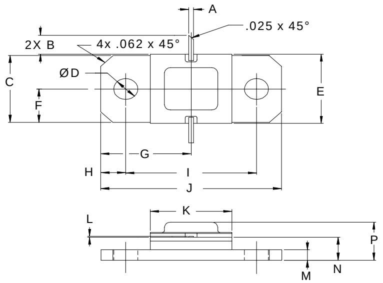
FEATURES:

- Internal Input/Output Matching Networks
- **P_G** = 7.0 dB at 350 W/1150 MHz
- ***Omnigold***™ Metalization System
- 3:1 Load VSWR Capability

MAXIMUM RATINGS

I_C	40 A
V_{CC}	55 V
P_{DISS}	1450 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	0.12 °C/W

PACKAGE STYLE .400 2NL FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.020 / 0.51	.030 / 0.76
B	.100 / 2.54	
C	.376 / 9.55	.396 / 10.06
D	.110 / 2.79	.130 / 3.30
E	.395 / 10.03	.407 / 10.34
F	.193 / 4.90	
G	.450 / 11.43	
H	.125 / 3.18	
I	.640 / 16.26	.660 / 16.76
J	.890 / 22.61	.910 / 23.11
K	.395 / 10.03	.415 / 10.54
L	.004 / 0.10	.007 / 0.18
M	.052 / 1.32	.072 / 1.83
N	.118 / 3.00	.131 / 3.33
P		.230 / 5.84

ORDER CODE: ASI10566

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I_C = 50 mA	65			**V**
BV_{EBO}	I_E = 25 mA	2.5			**V**
h_{FE}	V_{CE} = 5.0 V I_C = 1.0 A	10		120	**---**
P_G **η_C**	V_{CC} = 50 V P_{OUT} = 350 W f = 960-1215 MHz P_{IN} = 70 W	7.0 38	7.5 40	---	**dB** **%**

	Zin		ZCL	
Frequency	R	jx	R	jx
960	1.87	2.58	1.2	2.92
1030	1.96	1.92	1.06	2.71
1090	2.12	1.27	0.96	2.47
1150	2.33	0.65	0.91	2.3
1215	2.67	0.03	0.89	2.03